Schottky barrier diode

RB063L-30

●**Applications**

High frequency rectification
For switching power supply

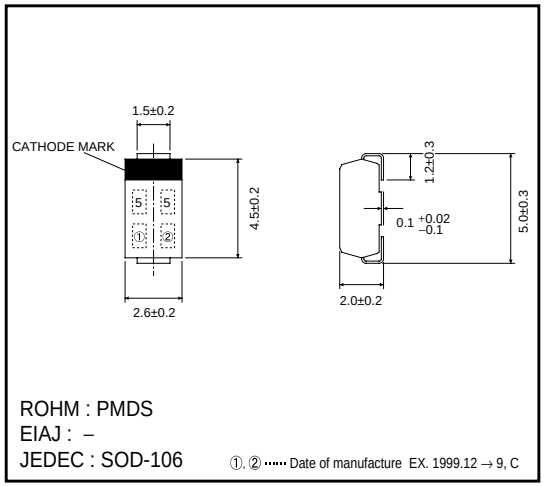
●**Features**

1) Compact power mold type. (PMDS)
2) Ultra low V_F / Low I_R.
3) V_{RM}=30V guaranteed.

●**Construction**

Silicon epitaxial planar

●**External dimensions** (Units : mm)



●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	30	V
DC reverse voltage	V_R	30	V
Mean rectifying current ∗	I_O	2	A
Peak forward surge current (60Hz·1∽)	I_{FSM}	70	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−40~+125	°C

∗ 180° half sine wave when mounted on glass epoxy PCBs.

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.395	V	I_F=2.0A
Reverse current	I_R	–	–	200	μA	V_R=30V

●**Electrical characteristic curves** (Ta=25°C)

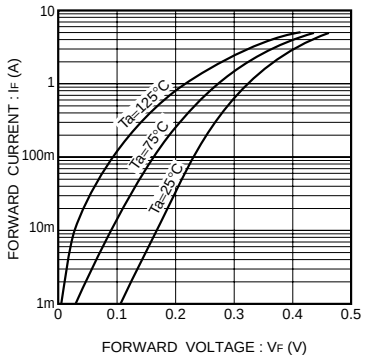


Fig.1 Forward characteristics

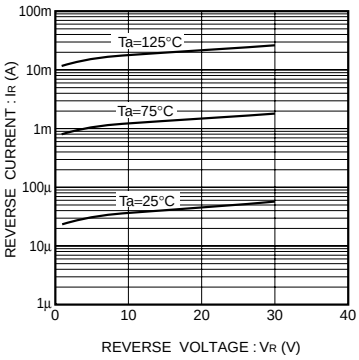


Fig.2 Reverse characteristics

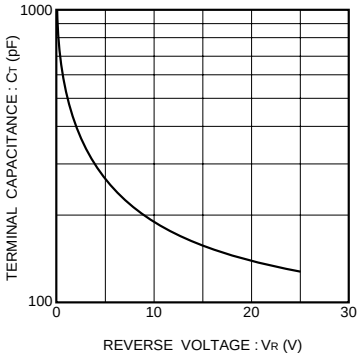


Fig.3 Capacitance between terminals characteristics

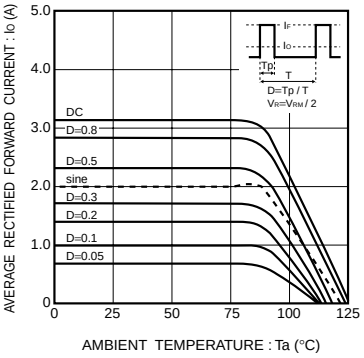


Fig.4 Derating curve (I_O - Ta) (When mounted on alumina PCBs)

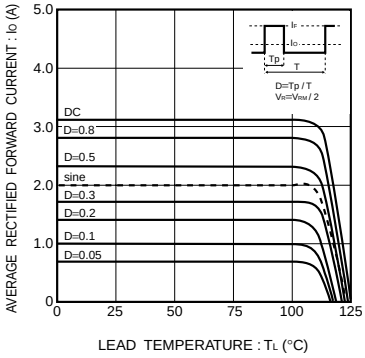


Fig.5 Derating curve (I_O - T_L) (When mounted on alumina PCBs)

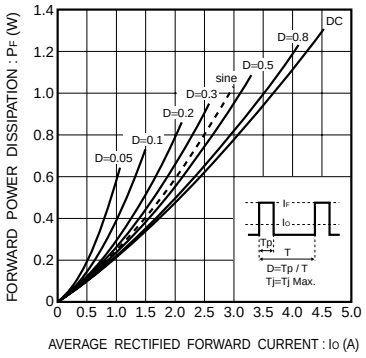


Fig.6 Forward power dissipation characteristics

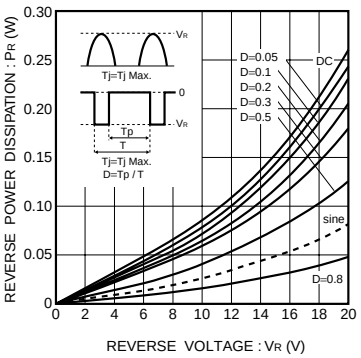


Fig.7 Reverse power dissipation characteristics

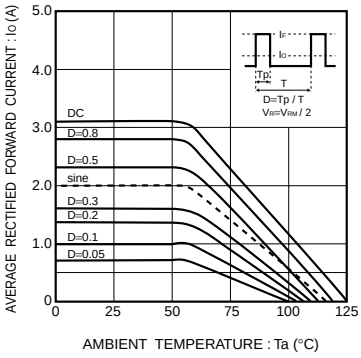


Fig.8 Derating curve (I_O - Ta) (when mounted on glass epoxy PCBs)